AMENDMENTS TO THE CLAIMS

Claims 1-8. (Canceled)

9. (Currently Amended) A heterojunction bipolar transistor comprising:

a semiconductor substrate of a first conductivity type including a collector region;

a base region formed on said substrate including a first base region doped with a non-dopant having a first concentration and a second base region doped with said non-dopant having a second concentration;

an emitter region formed over said base region including a first emitter polysilicon layer in-situ doped with a dopant having a first concentration and a second emitter polysilicon layer in-situ doped with said dopant having a second concentration; and

an emitter-base junction region formed by out-diffusion of said dopant from at least one of said first and second emitter polysilicon layers.

10. (Original) The heterojunction bipolar transistor of claim 9, wherein said base region comprises SiGe.

11. (Currently Amended) The heterojunction bipolar transistor of claim 9, wherein said first base region and said first emitter polysilicon layer are formed closer to said emitter-base junction region than said second base region and said second emitter polysilicon layer.

12. (Original) The heterojunction bipolar transistor of claim 9, wherein said non-dopant comprises carbon.

13. (Previously Presented) The heterojunction bipolar transistor of claim 12, wherein said first carbon concentration is from about 8×10^{18} cm⁻³ to about 5×10^{19} cm⁻³, and said second carbon

concentration is from about 1.5×10^{19} cm⁻³ to about 7×10^{19} cm⁻³.

14. (Original) The heterojunction bipolar transistor of claim 9, wherein said dopant comprises arsenic.

15. (Original) The heterojunction bipolar transistor of claim 14, wherein said first arsenic concentration is from about $5x10^{19}$ cm⁻³ to about $3x10^{20}$ cm⁻³, and said second arsenic concentration is from about $1x10^{20}$ cm⁻³ to about $7x10^{20}$ cm⁻³.

Claims 16-22.